

## Supplementary Information

*Pan Li, Xiao Zhang, Jinghua Li, and Jie Liu\**

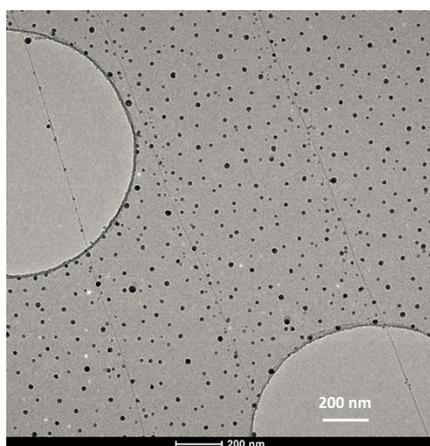
Department of Chemistry, Duke University, Durham, North Carolina 27708, United States

### **I. Transfer of SWNTs grown on ST-cut quartz onto SiO<sub>x</sub>/Si wafers.**

The transfer process has been adapted from Ref. S1<sup>1</sup> with some modifications. It consists of six steps.

1. Spin-cast a drop of 8% poly (methyl methacrylate) (495K molecular weight) (PMMA) solution in anisole on SWNTs/quartz at 4000 rpm for 30 sec. to form a PMMA layer.
2. Bake the substrate at 140°C for 15 min.
3. Immerse the PMMA/SWNTs/quartz substrate in boiling KOH (1 mol/L) aqueous solution for 10 min. The PMMA/SWNTs film should be peeled off from the quartz at the end of this step.
4. Take the film from the KOH solution, wash the film with water, and then carefully put onto a TEM grid.
5. Bake the PMMA/SWNTs/grid at 140°C for 2 min.
6. Bake the PMMA/SWNTs/grid at 400°C for 1h in a flow of 100 sccm Ar and 100 sccm H<sub>2</sub> to obtain well-aligned SWNTs on the TEM grid.

Figure S1 shows a typical transfer result. No changes of the alignment of the SWNTs have been found after the transfer.

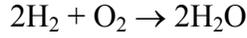


**Figure S1.** HRTEM image of the transferred SWNT array grown by Cu catalyst on quartz. The good alignment was maintained after transfer process, which had no solvent involved during the removal of PMMA polymer. The

black dots were formed by aggregation of residual PMMA.

## II. Water concentration calculation

Combustion of H<sub>2</sub> follows the following equation



With only small amount of H<sub>2</sub> introduced, the O<sub>2</sub> in air is considered as excess reactant, so the amount of H<sub>2</sub>O product is determined by the amount of H<sub>2</sub>.

So the concentration of H<sub>2</sub>O vapor C<sub>H<sub>2</sub>O</sub> produced by the reaction in the CVD chamber is:

$$C_{\text{H}_2\text{O}} = m_{\text{H}_2\text{O}} / V_{\text{total}} \quad (1)$$

Where m<sub>H<sub>2</sub>O</sub> is mass of the water, V<sub>total</sub> is the volume of the quartz tube used for the annealing and the CVD growth, which is 600 ml;

$$m_{\text{H}_2\text{O}} = n_{\text{H}_2\text{O}} * M_{\text{H}_2\text{O}} \quad (2)$$

where n<sub>H<sub>2</sub>O</sub> is the mole number of water, and M<sub>H<sub>2</sub>O</sub> is molar mass of water, 18 g/mol, then we have

$$C_{\text{H}_2\text{O}} = n_{\text{H}_2\text{O}} * 18 \text{ g/mol} / 600 \text{ ml}$$

According to the chemical equation,

$$n_{\text{H}_2\text{O}} = n_{\text{H}_2} \quad (3)$$

and

$$n_{\text{H}_2} \approx V_{\text{H}_2} / R = v_{\text{H}_2} * t / R \quad (4)$$

Where V<sub>H<sub>2</sub></sub> is the volume of H<sub>2</sub> introduced into the system, t is the duration of H<sub>2</sub> introduction, and the flow rate of H<sub>2</sub> v<sub>H<sub>2</sub></sub>, is fixed at 180 sccm. H<sub>2</sub> is treated as ideal gas here, so R= 22.4 L/mol.

Then we get

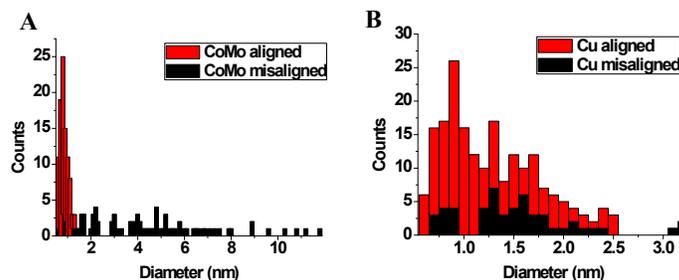
$$C_{\text{H}_2\text{O}} = v_{\text{H}_2} * t / R * M_{\text{H}_2\text{O}} / V_{\text{total}} = 180 \text{ ml/min} * t(\text{min}) / 22.4 \text{ L/mol} * 18 \text{ g/mol} / 600 \text{ ml} \quad (5)$$

$$C_{\text{H}_2\text{O}} = 4.0 * t(\text{min}) \text{ g/L} \quad (6)$$

When H<sub>2</sub> is introduced for 20 seconds, the C<sub>H<sub>2</sub>O</sub> will be 1.3 g/ L, which is 1300g/ m<sup>3</sup>, which is much higher than saturated concentration of water vapor in air at room temperature, 18.5 g/m<sup>3</sup>.

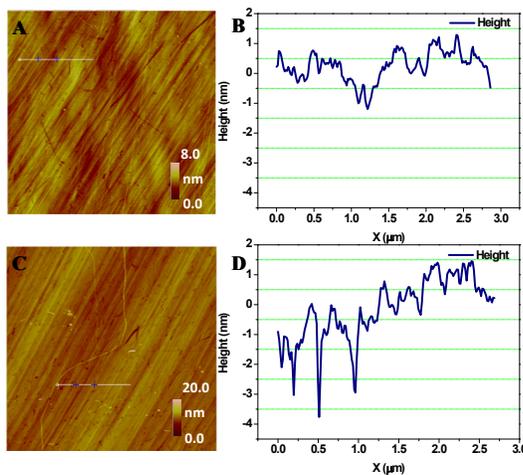
We chose to introduce water by  $H_2$  combustion because of the high water vapor concentration it produced at the moment of the reaction happening.

### III. Statistic on the diameter distribution of both aligned and kinked SWNTs in Cu and CoMo catalyzed system.

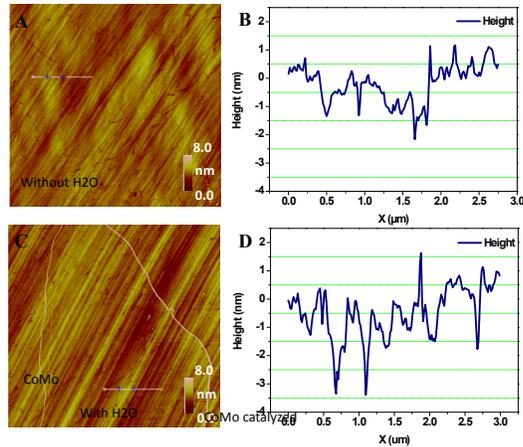


**Figure S2.** The diameter distribution of both aligned and misaligned (kinked) SWNTs in Cu (A) and CoMo (B) catalyzed system. The systems using the same catalyst were considered together regardless of the annealing condition. The diameter of the SWNTs were measured by AFM.

### IV. Investigation of etching effect of water on quartz substrate under high temperature.

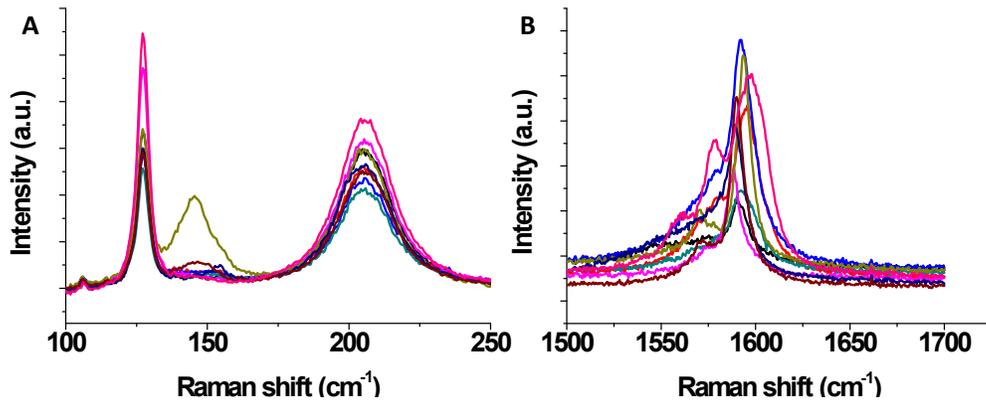


**Figure S3.** AFM images of SWNTs grown on quartz substrate by using Cu-w (A), Cu (C) as catalyst respectively; and corresponding section analysis results of the substrate morphology with(D) and without(B) water during catalyst annealing process. The AFM image sizes are  $8 \times 8 \mu\text{m}$ . The section plot shows the height profile of selected area along the white line in AFM image. The section analysis line was drawn based on the scan direction of the AFM probes.



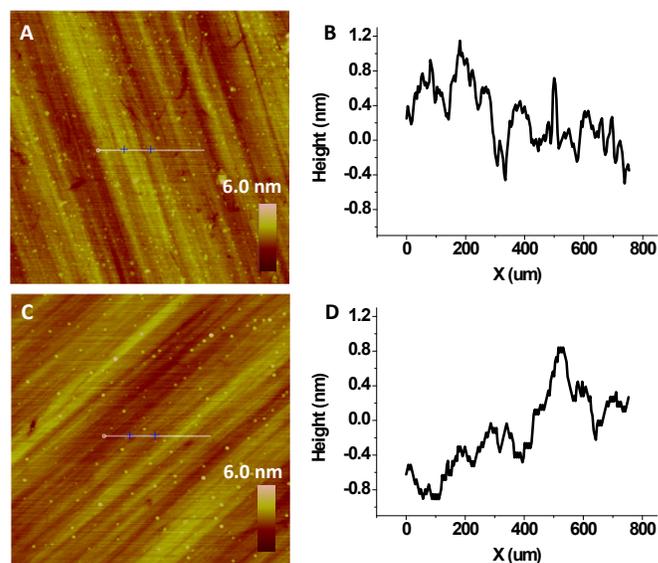
**Figure S4.** AFM images of SWNTs grown on quartz substrate by using CoMo-w (A), CoMo (C) as catalyst respectively; and corresponding section analysis results of the substrate morphology with(D) and without(B) water during catalyst annealing process. The AFM image sizes are  $8 \times 8$   $\mu\text{m}$ . The section plot shows the height profile of selected area between the blue crosses on the white line in AFM image. The section analysis line was drawn based on the scan direction of the AFM probes.

## V. Raman characterization of SWNTs on quartz substrate.

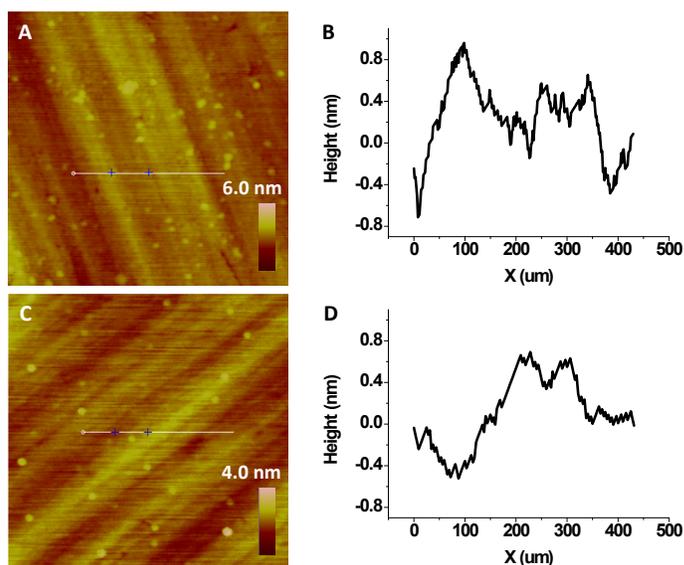


**Figure S5.** The Raman spectra of SWNTs grown by Co1Mo3-w catalyst. The excitation was 633 nm laser. (A) RBM region; and (B) G-band.

## VI. Investigation of influence of annealing on surface morphology of quartz substrate.



**Figure S6.** AFM images and corresponding section analysis results of the substrate morphology of quartz substrate before (A, B) and after (C, D) the annealing process. The AFM image sizes are  $2 \times 2 \mu\text{m}$ . The section plot shows the height profile of selected area along the white line in AFM image. The section analysis line was drawn based on the scan direction of the AFM probes. The randomly distributed particles were contaminant adsorbed on the substrate after being stored for long time.



**Figure S7.** AFM images and corresponding section analysis results of the substrate morphology of quartz substrate before (A, B) and after (C, D) the annealing process. The AFM image sizes are  $800 \times 800 \text{ nm}$ . The section plot shows the height profile of selected area along the white line in AFM image. The section analysis line was drawn based on the scan direction of the AFM probes. The randomly distributed particles were contaminant adsorbed on the substrate after being stored for long time.

## Notes and references

1. L. Jiao, B. Fan, X. Xian, Z. Wu, J. Zhang and Z. Liu, *Journal of the American Chemical Society*, 2008, **130**, 12612-12613.

